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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										備考		
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μS)	f _{αb} f _r * (Mc)		C _{ob} (pF)	r _{bb'} h _{ie} (real)* (Ω)
1	2	3	4	5					6		7		8				9	10		11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
- 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外 形	備 考				
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値		直流又はパルス h _{FE}			バイアス			h _{fe} h _β *	h _{ie} h _{iβ} *	h _{re} h _{rβ} *			h _{oe} h _{oβ} *	f _β f _β *	C _{ob} C _{ob1}	T _{bb} h _{bb} (real)*
									(μA)	V _{CE} (V)	I _C (mA)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)	(Ω)									
* 2SC1451	富士通	RF	Si.EP	150	5	50	700	175	1	140	150	5	10	5	-10	t _{on} < 1μS, t _{off} < 10μS t _{stg} < 9.5μS				130*	2	70*	248		
* 1452	"	"	"	150	5	50	700	175	1	140	150	5	10	5	-10	t _{on} < 1μS, t _{off} < 10μS t _{stg} < 9.5μS				130*	2	70*	248		
* 1453	東芝	"	"	55	5	100	200	150	0.1	30	120	1	10	10	-1					150*	5	20	195		
* 1454	サンケン	PA	Si.TMe	300	6	4A	50W (T _c =25°C)	150	1mA	300	>20	5	1A	12	-100					10*			102		
* 1455																									
* 1456	日電	PA	Si.TP	300	7	200	15W (T _c =25°C)	150	0.1	200	80	10	10	30	-10					80*	3.8	30	99		
* 1457	"	RF	Si.E	35	3	150	800	200	0.1	20	100	10	50	10	-50	NF < 3.2dB (f=200MHz, V _{CE} =10V, I _C =20mA)				2700*	C _{rr}	45*	85B		
* 1458	"	"	"	20	3	50	300	200	0.1	10	100	5	30	5	-15	S ₂₁ _r = 9dB (f=1GHz)				3000*	C _{rr}	30*	130		
* 1459	富士通	"	Si.EP	15	3	70	300	175	0.5	10	80	6	40	6	-40					5000*	1	25*	199		
* 1460	"	"	"	15	3	30	250	175	0.5	10	80	6	10	6	-10	NF = 4.5dB (f=2GHz, V _{CE} =6V, I _C =4mA)				4500*	0.7	25*	199		
* 1461	"	"	"	15	3	40	250	175	0.5	10	80	6	20	6	-20					4500*	0.8	25*	199		
* 1462	"	"	"	15	3	30	250	175	0.5	10	80	6	15	6	-15	NF = 3.5dB (f=2GHz, V _{CE} =6V, I _C =4mA)				6500*	0.7	25*	199		
* 1463	"	SW	Si.T	450	5	4A	75W (T _c =25°C)	175	10	150	18	5	1A	6	-300	t _{on} < 5μs, t _{off} < 3μs t _{stg} < 5μs				25*	125	5*	102		
* 1464	"	PA	Si.EP	50	3.5	500	4W (T _c =25°C)	175	250	20	80	5	200	12	-100	P _o = 1.2W (f=175MHz, V _{cc} =12V, P _i =50mW)				1300*	3.5		84C		
* 1465	"	"	"	50	3.5	500	7W (T _c =25°C)	175	250	20	80	5	200	12	-100	P _o = 1.8W, η = 55% (f=0.7GHz, V _{cc} =24V, P _i =0.3W)				1600*	4.5		231		
* 1466	新電元	SW	Si.DB	450	4	3A	30W (T _c =25°C)	150	1mA	450	16	5	1.5A	10	1A	t _{on} < 2μS, t _{off} < 2μS t _{stg} < 4μS				10*	60		204		
* 1467	"	"	"	500	4	3A	30W (T _c =25°C)	150	1mA	500	12	5	1.5A	10	1A					10*	60		204		
* 1468	"	"	"	450	4	10A	100W (T _c =25°C)	150	10mA	450	16	5	5A	10	1A					10*	300		102		
* 1469	"	"	"	500	4	10A	100W (T _c =25°C)	150	10mA	500	12	5	5A	10	2A					10*	300		102		
* 1470	"	"	"	450	4	30A	200W (T _c =25°C)	150	10mA	450	16	5	10A	10	2A					10*	700		266		
* 1471	"	"	"	500	4	30A	200W (T _c =25°C)	150	10mA	500	12	5	10A	10	2A					10*	700		266		
* 1472	日立	RF	Si.EP	40	10	300	500	125	0.1	30	2000~ 100000	5	10	5	-10	t _{on} = 60nS, t _{off} = 800nS t _{stg} = 350nS				>50*	<10	220	138		
* 1473	松下	PA	"	250	5	70	600	125	2	12	120	10	5	10	-10					80*	5	C _c P _{ob} 60pS	138		
* 1474	ソニー	RF.PA	Si.PaMe	16	6	2A	750	120	0.2	16	300	2	100	2	-10					60*	30	C _c P _{ob} 600pS	259	2SA772 とコソアリ	
* 1475	"	"	"	100	6	1A	750	120	0.2	25	300	2	100	2	-10					80*	16	C _c P _{ob} 300pS	259	2SA773 とコソアリ	
* 1476	東芝	PA	Si.EP	38		5A	40W (T _c =25°C)	175	1mA	15	50	5	1A			P _o = 22W (f=470MHz, V _{cc} =12.6V, P _i =12W)							135		
* 1477	サンケン	SW	Si.T	230	6	9A	80W (T _c =25°C)	150	1mA	230	20	4	5A			t _{on} < 1.5μS, t _{off} < 1μS t _{stg} < 4μS							102		
* 1478	松下	RF.LN	Si.EP	35	5	50	150	175	0.1	10	540	5	2	5	-2			5500	0.4	25	150*	2.2	70	243	
* 1479	富士通	PA	"	36	3.5	500	3W (T _c =25°C)	175	100	12	50	2	200	12	-100	P _o = 1.2W (f=175MHz, V _{cc} =12.5V, P _i =50mW)				1000*	4		84B		
* 1480	"	"	"	36	3.5	500	7W (T _c =25°C)	175	100	12	50	2	500	12	-100	P _o = 2.4W, η = 60% (f=470MHz, V _{cc} =12.5V, P _i =0.3W)				1200*	5		246		